

AM2520PD1BT09 Photodiode

DESCRIPTION

- Made with PIN silicon phototransistor chips

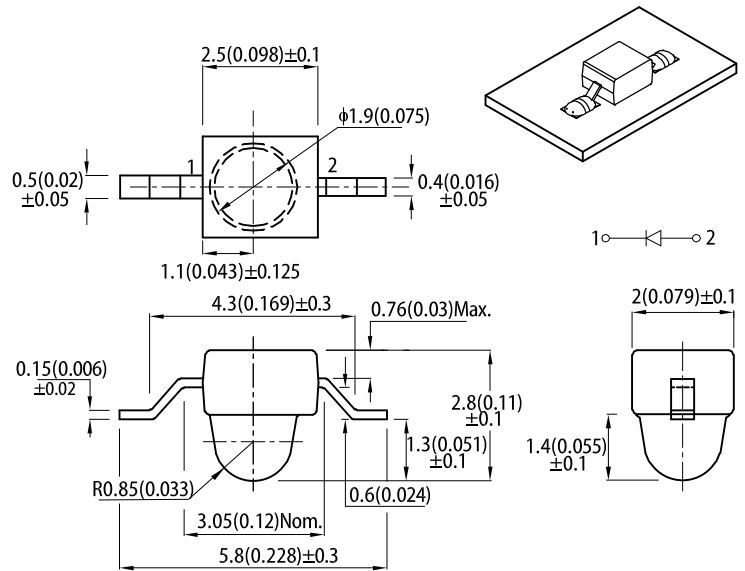
FEATURES

- Mechanically and spectrally matched to the infrared emitting LED lamp
- Moisture sensitivity level: 3
- Package: 1000 pcs / reel
- RoHS compliant

APPLICATIONS

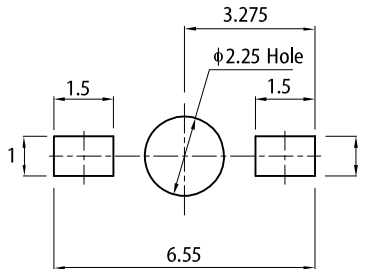
- Infrared applied systems
- Optoelectronic switches
- Photodetector control circuits
- Sensor technology

PACKAGE DIMENSIONS



RECOMMENDED SOLDERING PATTERN

(units : mm; tolerance : ± 0.1)



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is ±0.25(0.01") unless otherwise noted.
3. The specifications, characteristics and technical data described in the datasheet are subject to change without prior notice.
4. The device has a single mounting surface. The device must be mounted according to the specifications.

ABSOLUTE MAXIMUM RATINGS at $T_A=25^{\circ}\text{C}$

Parameter	Max.Ratings	Units
Power Dissipation	150	mW
Operating Temperature	-40 to +85	$^{\circ}\text{C}$
Storage Temperature	-40 to +85	$^{\circ}\text{C}$

Note:

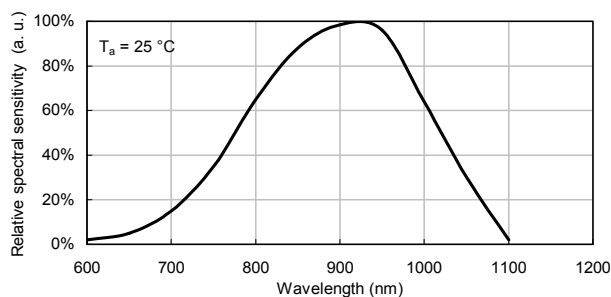
1. Relative humidity levels maintained between 40% and 60% in production area are recommended to avoid the build-up of static electricity – Ref JEDEC/JESD625-A and JEDEC/J-STD-033.

ELECTRICAL / OPTICAL CHARACTERISTICS at $T_A=25^\circ\text{C}$

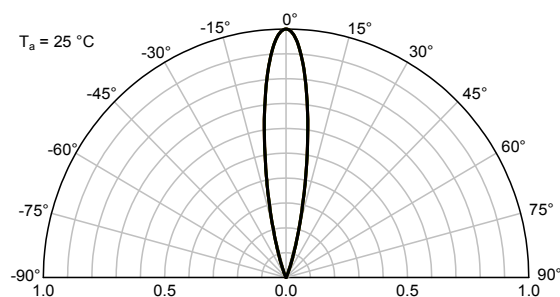
Parameter	Symbol	Min.	Typ.	Max.	Units	Test Conditions
Reverse Break down Voltage	$V_{(BR)R}$	33	170	-	V	$I_R = 100\mu\text{A}$ $H = 0\text{mW}/\text{cm}^2$
Reverse Dark Current	$I_{D(R)}$	-	-	10	nA	$V_R = 10\text{V}$ $H = 0\text{mW}/\text{cm}^2$
Open Circuit Voltage	V_{OC}	-	390	-	mV	$\lambda = 940\text{nm}$ $H = 5\text{mW}/\text{cm}^2$
Rise Time	T_R	-	6	-	nS	$V_R = 10\text{V}$ $\lambda = 940\text{nm}$ $R_L = 1000\Omega$
Fall Time	T_F	-	6	-	nS	
Light current	I_S	0.7	1.5	-	μA	$V_R = 5\text{V}$ $E_e = 0.08\text{mW}/\text{cm}^2$ $\lambda = 940\text{nm}$
Total Capacitance	C_T	-	5	-	pF	$V_R = 10\text{V}$ $F = 1\text{MHZ}$ $H = 0\text{mW}/\text{cm}^2$
Range of spectral bandwidth	$\lambda_{0.1}$	670	-	1070	nm	-
Wavelength of peak sensitivity	λ_p	-	940	-	nm	-
Angle of half sensitivity	$2\theta_{1/2}$	-	20	-	deg	-

TECHNICAL DATA

RELATIVE SPECTRAL SENSITIVITY vs. WAVELENGTH

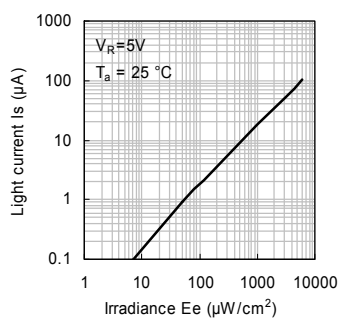


RELATIVE RADIANT SENSITIVITY vs. ANGULAR DISPLACEMENT

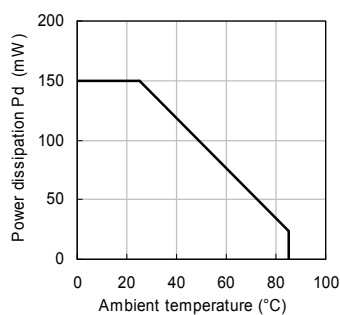


PHOTODIODE

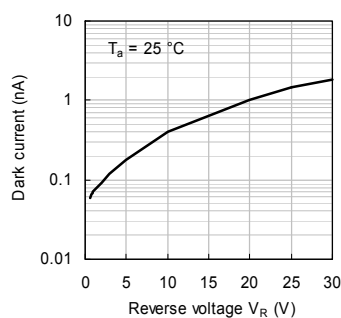
Light Current vs. Irradiance



Power Dissipation vs. Ambient Temperature



Dark Current vs. Reverse Voltage



Dark Current vs. Ambient Temperature

